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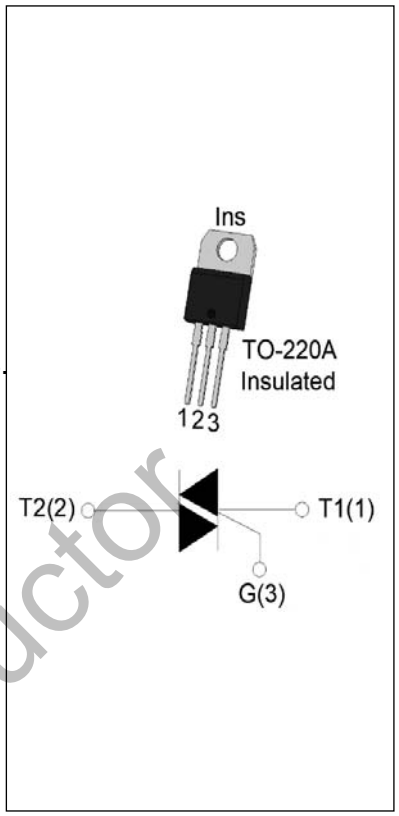
BTA30-1200BW 30A TRIAC

DESCRIPTION:

The BTA30-1200BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. BTA30-1200BW snubberless triac is especially recommended for use on inductive loads. By using an internal ceramic pad, BTA30-1200BW provides a rated insulation voltage of 2500 VRMS, complying with UL standards. Package TO-220A is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	30	A
V_{DRM} /V_{RRM}	1200	V
$I_{GT\ I/II/III}$	50/50/50	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	℃
Operating junction temperature range	T_j	-40-125	℃
Repetitive peak off-state voltage (T_j=25℃)	V_{DRM}	1200	V
Repetitive peak reverse voltage (T_j=25℃)	V_{RRM}	1200	V
RMS on-state current (T_C≤75℃)	$I_{T(RMS)}$	30	A
Non repetitive surge peak on-state current (full cycle , t_p=20ms , T_j=25℃)	I_{TSM}	300	A
Non repetitive surge peak on-state current (full cycle , t_p=16.6ms , T_j=25℃)		330	
I^2t value for fusing (t_p=10ms , T_j=25℃)	I^2t	450	A^2s
Critical rate of rise of on-state current (I_G=2×I_{GT} , f=100Hz , T_j=125℃)	dI/dt	100	A/μs
Peak gate current (t_p=20μs , T_j=125℃)	I_{GM}	4	A
Average gate power dissipation (T_j=125℃)	$P_{G(AV)}$	0.5	W

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Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25℃; non-repetitive,off-state;FIG.7)	V_{pp}	2.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	Ⅰ-Ⅱ-Ⅲ	MAX.	50	mA
V_{GT}		Ⅰ-Ⅱ-Ⅲ	MAX.	1.3	V
V_{GD}	V_D =V_{DRM} T_j =125℃ R_L =3.3KΩ	Ⅰ-Ⅱ-Ⅲ	MIN.	0.15	V
I_L	I_G =1.2I_{GT}	Ⅰ-Ⅲ	MAX.	90	mA
		Ⅱ		100	
I_H	I_T =500mA		MAX.	80	mA
dV/dt	V_D=800V Gate Open T_j =125℃		MIN.	1200	V/μs
(dI/dt)c	(dV/dt)c=20V/μs T_j=125℃		MIN.	25	A/ms
t_{on}	I_G=80mA I_A=400mA I_R=40mA T_j=25℃		TYP.	10	μs
t_{off}				70	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =42A t_p=380μs	T_j=25℃	1.5	V
V_{TO}	Threshold voltage	T_j=125℃	0.73	V
R_D	Dynamic resistance	T_j=125℃	25	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25℃	10	μA
I_{RRM}		T_j=125℃	4	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.2	℃/W
$R_{th(j-a)}$	junction to ambient (AC)	60	℃/W

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FIG.1 Maximum power dissipation versus RMS on-state current

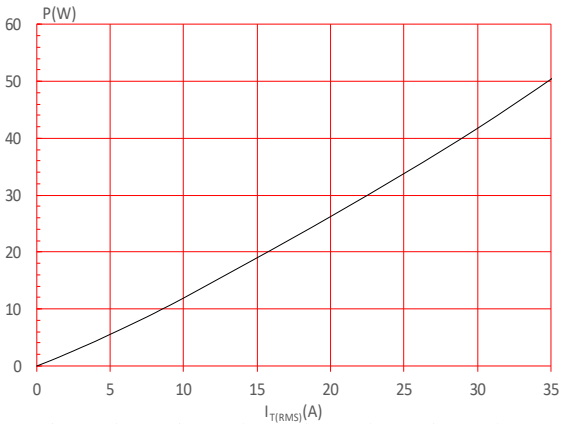

FIG.2: RMS on-state current versus case temperature

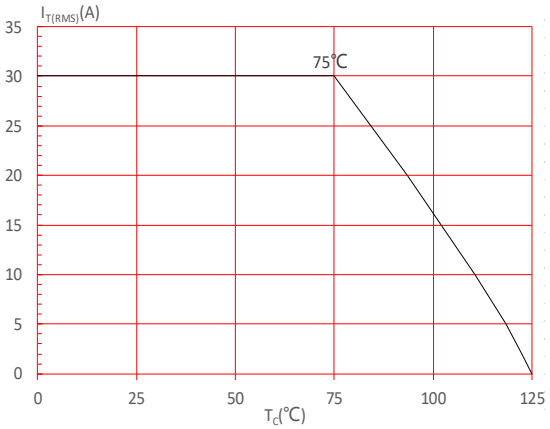

FIG.3: Surge peak on-state current versus number of cycles

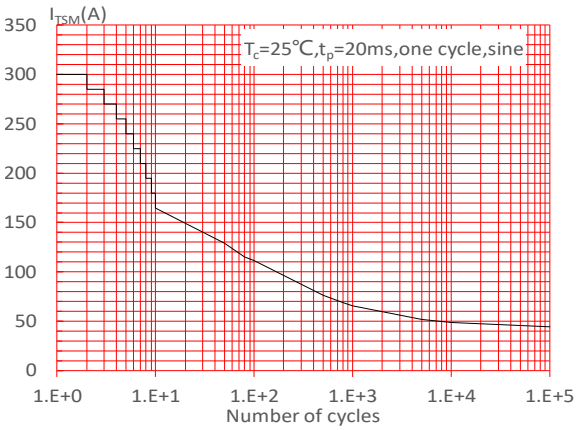

FIG.4: On-state characteristics

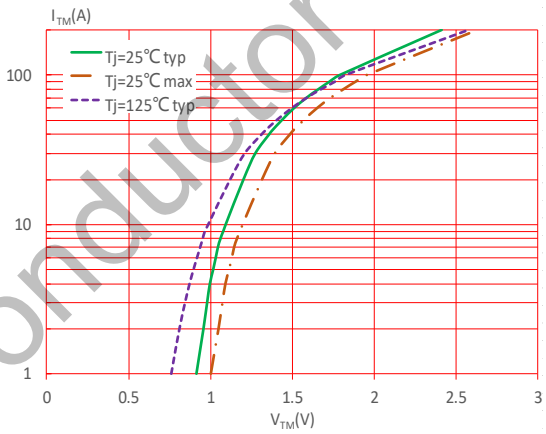

FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p<20ms, and corresponding value of I^2t (dI/dt<100A/μs)

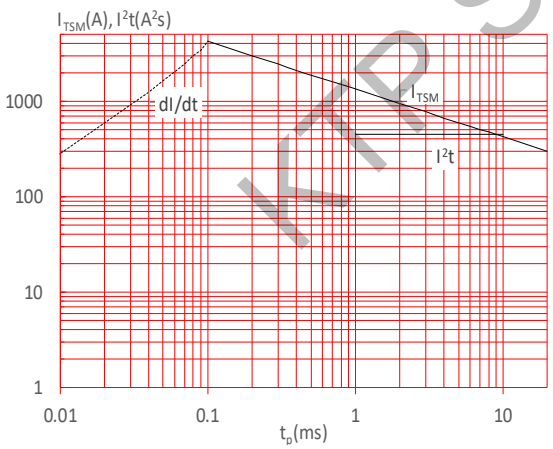

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

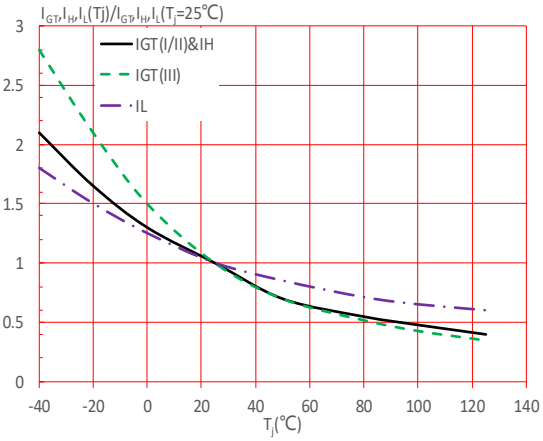

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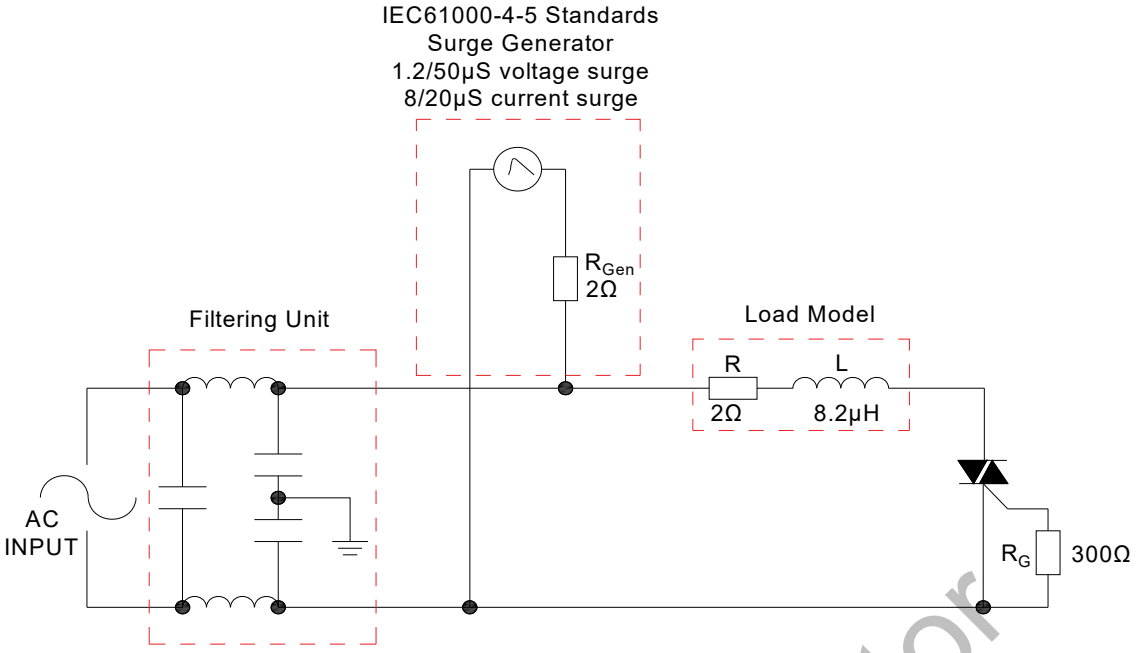
FIG.7：Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



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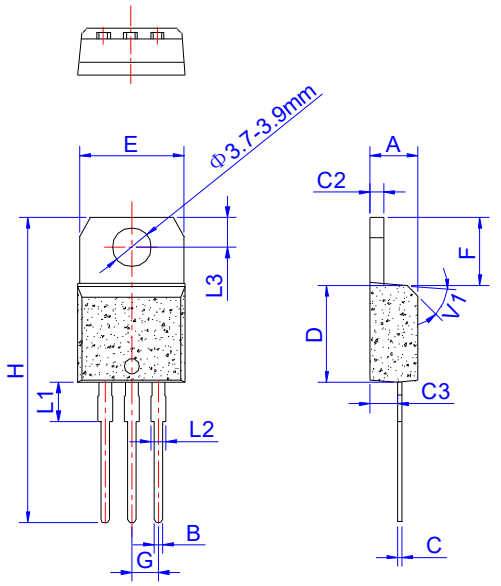
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		Ⅰ-Ⅱ-Ⅲ			
BTA30-1200BW	1200	50	TO-220A(Ins)	50	Tube

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.25		6.85	0.246		0.270
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.45		4.05	0.136		0.159
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

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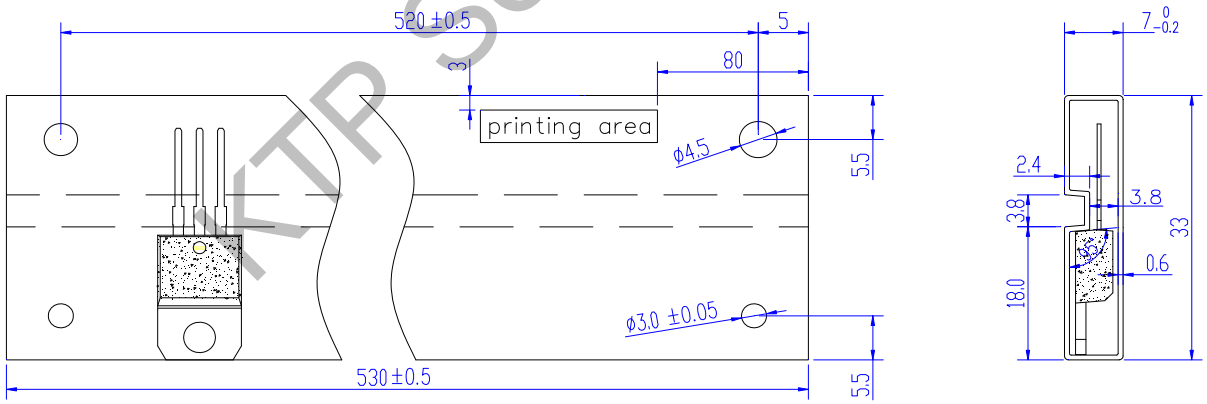
DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220A	TUBE	50	1,000	5,000